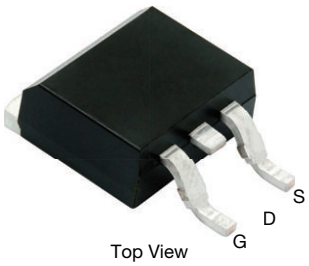
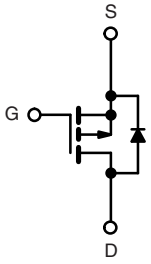
Automotive P-Channel 40 V (D-S) 175 °C MOSFET

TO-263



Top View



P-Channel MOSFET

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

RoHS COMPLIANT

HALOGEN FREE

PRODUCT SUMMARY	
V_{DS} (V)	-40
$R_{DS(on)}$ (Ω) at V_{GS} = -10 V	0.00300
$R_{DS(on)}$ (Ω) at V_{GS} = -4.5 V	0.00380
I_D (A)	-120
Configuration	Single
Package	TO-263

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current [a]	T_C = 25 °C	I_D	-120	A
	T_C = 125 °C		-120	
Continuous Source Current (Diode conduction) [a]		I_S	-120	
Pulsed Drain Current [b]		I_{DM}	-300	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	-60	
Single Pulse Avalanche Energy		E_{AS}	180	mJ
Maximum Power Dissipation [b]	T_C = 25 °C	P_D	375	W
	T_C = 125 °C		125	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB mount [c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR4 material).

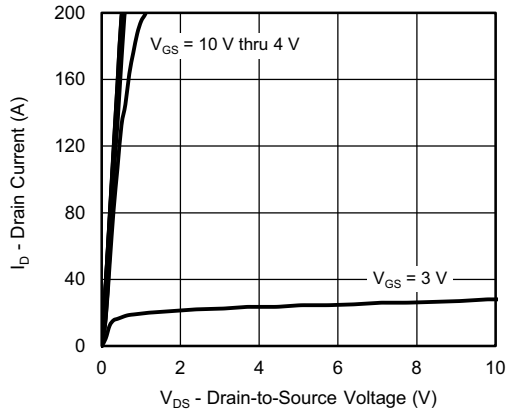
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA		-40	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA		-1.5	-2.0	-2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = -40 V	-	-	-1	µA
		V_{GS} = 0 V	V_{DS} = -40 V, T_J = 125 °C	-	-	-50	
		V_{GS} = 0 V	V_{DS} = -40 V, T_J = 175 °C	-	-	-450	
On-State Drain Current [a]	$I_{D(on)}$	V_{GS} = -10 V	V_{DS} ≤ -5 V	-100	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V	I_D = -30 A	-	0.00250	0.00300	Ω
		V_{GS} = -10 V	I_D = -30 A, T_J = 125 °C	-	-	0.00440	
		V_{GS} = -10 V	I_D = -30 A, T_J = 175 °C	-	-	0.00520	
		V_{GS} = -4.5 V	I_D = -25 A	-	0.00316	0.00380	
Forward Transconductance [b]	g_{fs}	V_{DS} = -15 V, I_D = -25 A		-	123	-	S
Dynamic [b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = -25 V, f = 1 MHz	-	30 000	39 000	pF
Output Capacitance	C_{oss}			-	1850	2500	
Reverse Transfer Capacitance	C_{rss}			-	1550	2100	
Total Gate Charge [c]	Q_g	V_{GS} = -10 V	V_{DS} = -20 V, I_D = -80 A	-	527	800	nC
Gate-Source Charge [c]	Q_{gs}			-	89	-	
Gate-Drain Charge [c]	Q_{gd}			-	100	-	
Gate Resistance	R_g	f = 1 MHz		1	2.26	3.5	Ω
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = -20 V, R_L = 0.3 Ω I_D ≅ -80 A, V_{GEN} = -10 V, R_g = 1 Ω		-	21	35	ns
Rise Time [c]	t_r			-	30	50	
Turn-Off Delay Time [c]	$t_{d(off)}$			-	250	400	
Fall Time [c]	t_f			-	165	300	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed Current [a]	I_{SM}			-	-	-300	A
Forward Voltage	V_{SD}	I_F = -80 A, V_{GS} = 0 V		-	-0.85	-1.5	V
Body diode reverse recovery time	t_{rr}	I_F = -50 A, di/dt = 100 A/µs		-	70	140	ns
Body diode reverse recovery charge	Q_{rr}			-	134	270	nC
Reverse recovery fall time	t_a			-	43	-	ns
Reverse recovery rise time	t_b			-	35	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-4	-8	A

Notes

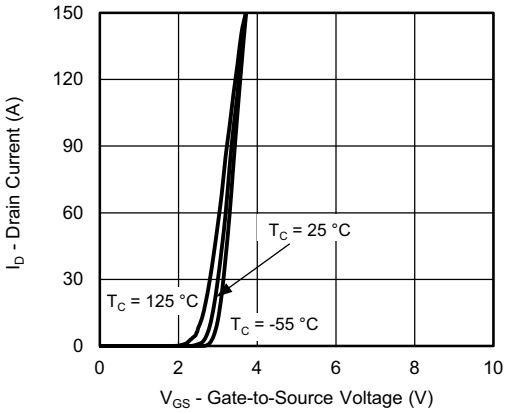
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

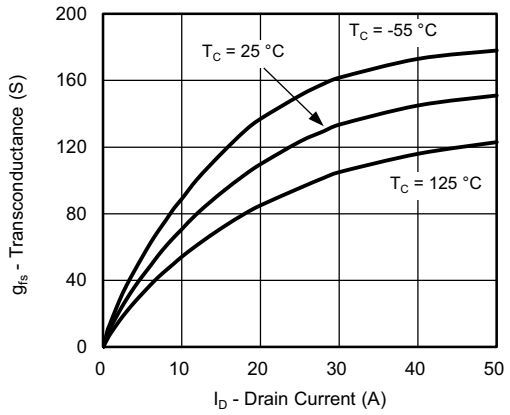
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



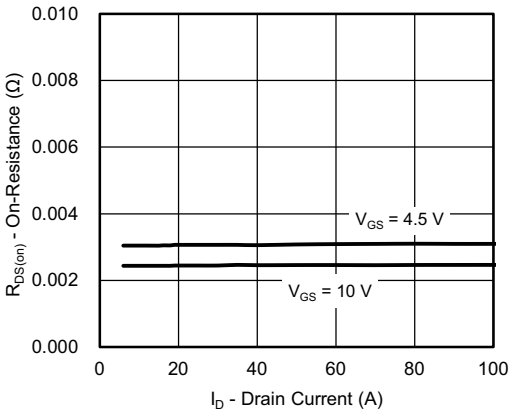
Output Characteristics



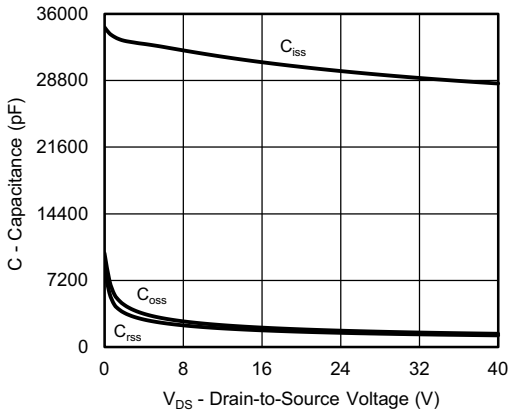
Transfer Characteristics



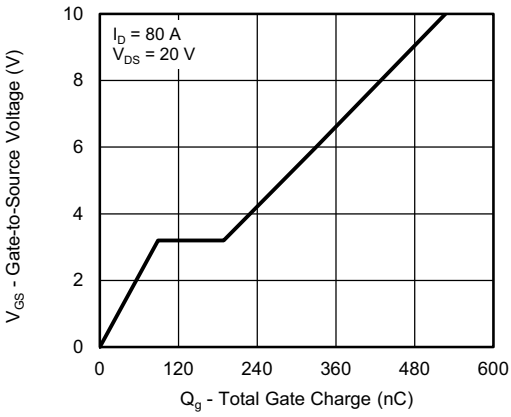
Transconductance



On-Resistance vs. Drain Current

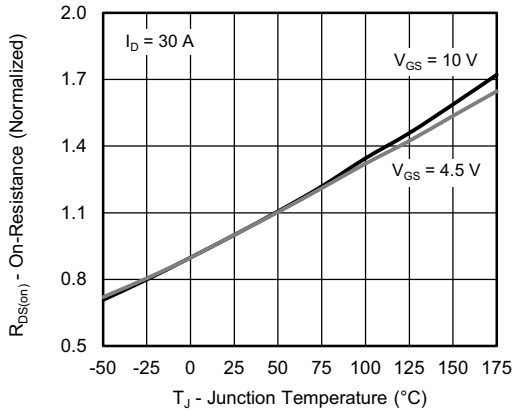


Capacitance

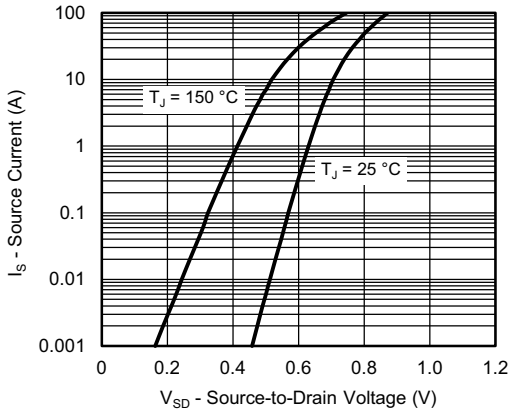


Gate Charge

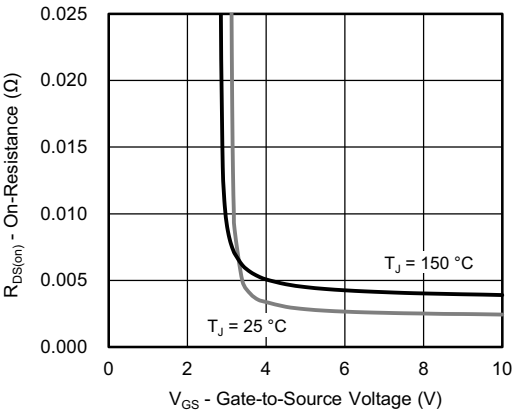
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



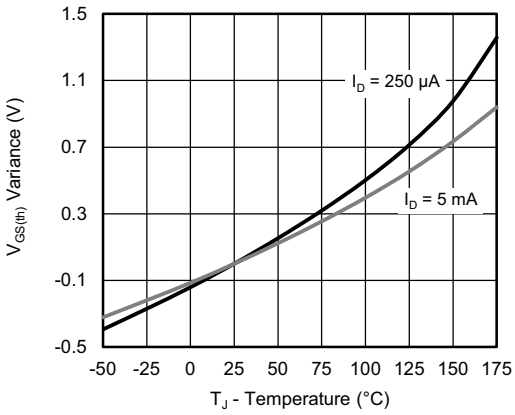
On-Resistance vs. Junction Temperature



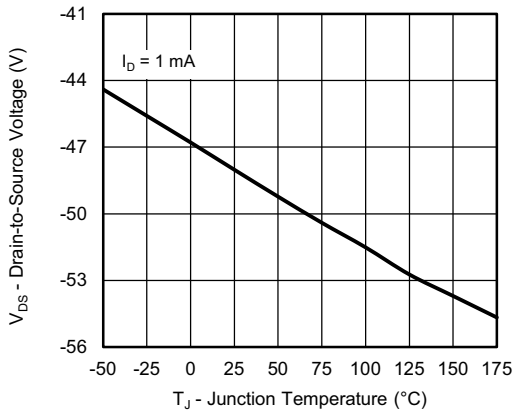
Source Drain Diode Forward Voltage



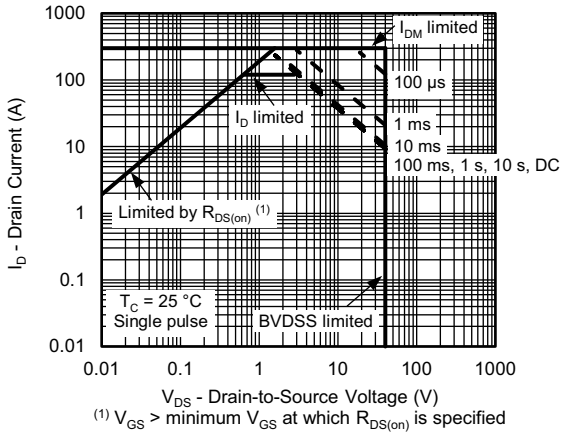
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

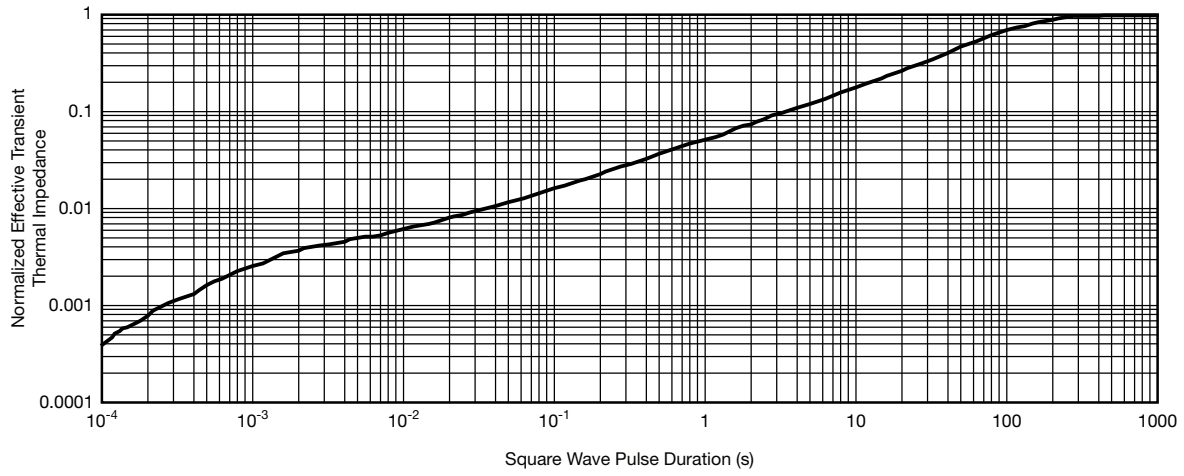


Drain Source Breakdown vs. Junction Temperature

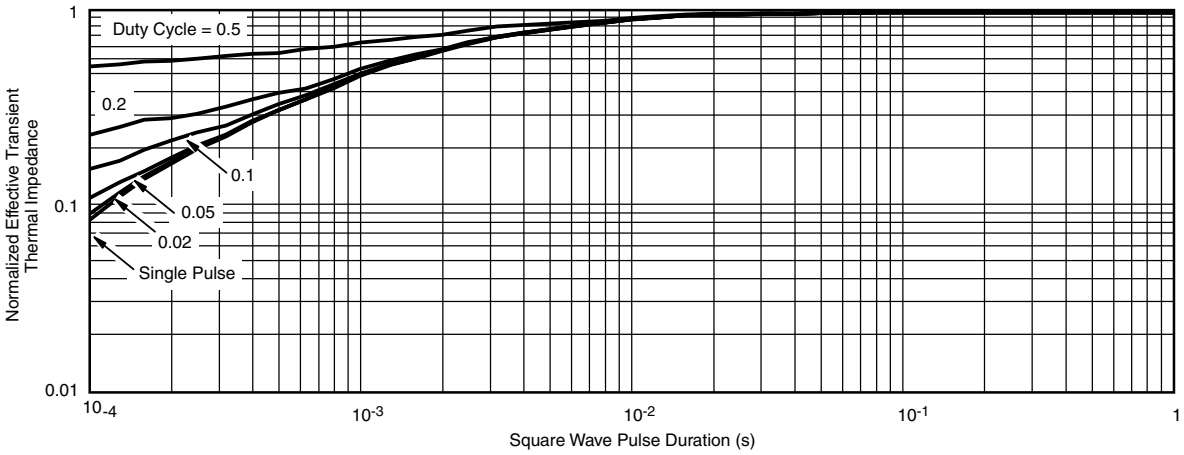


Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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